New Jersey Semi-Conductor Products, Inc.

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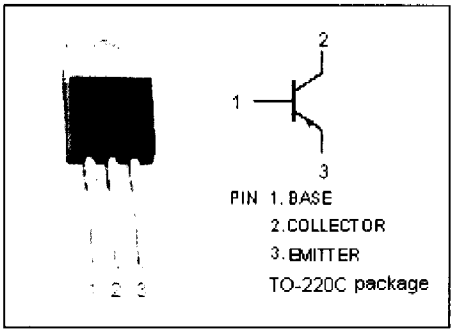
Silicon PNP Power Transistor

2SA634

DESCRIPTION

- High Collector Current I_C= -3A
- Collector-Emitter Breakdown Voltage-
  : $V_{(BR)CEO}$= -30V(Min)
- Good Linearity of h_{FE}
- Complement to Type 2SC1096

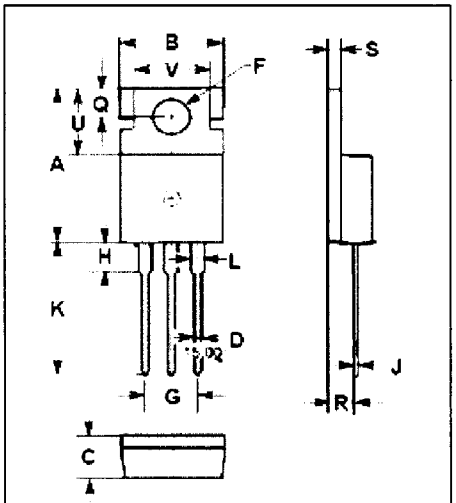


APPLICATIONS

- Designed for output stages of 3~5 watts car radio sets and car stereo applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-40	V
V_{CEO}	Collector-Emitter Voltage	-30	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-3	A
I_{CP}	Collector Current-Peak	-6	A
I_B	Base Current-Continuous	-0.6	A
P_T	Collector Power Dissipation @ T_C=25℃	10	W
	Collector Power Dissipation @ T_a=25℃	1.2	
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃



DIM	mm MIN	mm MAX
A	15.50	15.90
B	9.90	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2.68	2.90
J	0.44	0.60
K	13.00	13.40
L	1.20	1.45
Q	2.70	2.90
R	2.30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -3A; I_B= -0.3A			-2.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= -3A; I_B= -0.3A			-2.0	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -30V; I_E= 0			-1.0	μ A
I_{EBO}	Emitter Cutoff Current	V_{EB}= -3V; I_C= 0			-1.0	μ A
h_{FE-1}	DC Current Gain	I_C= -20mA; V_{CE}= -5V	20			
h_{FE-2}	DC Current Gain	I_C= -1A; V_{CE}= -5V	40		250	
f_T	Current-Gain—Bandwidth Product	I_C= -0.1A; V_{CE}= -5V		55		MHz
C_{OB}	Output Capacitance	I_E= 0; V_{CB}= -10V, f= 1MHz		75		pF

◆ **h_{FE-2} Classifications**

N	M	L	K
40-60	50-100	80-160	120-250